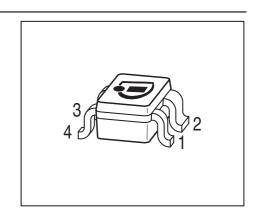


High Performance Bipolar NPN RF Transistor

- High transducer gain of typ. 14 dB @ 25 mA,6 GHz
- Low minimum noise figure of typ. 0.85 dB @ 6GHz
- High output compression of typ. 11 dBm @ 25 mA
- Pb-free (RoHS compliant) package
- For a wide range of non-automotive applications
 - 2nd and 3rd LNA stage and mixer stage in LNB
 - 5.8 GHz analog/digital cordless phone
 - Satellite radio SDARS
 - WLAN, WiMAX, UWB





ESD (Electrostatic discharge) sensitive device, observe handling precaution!

Туре	Marking	Pin Configuration			Package			
BF888	RYs	1=B	2=E	3=C	4=E	-	-	SOT343

Maximum Ratings at T_A = 25 °C, unless otherwise specified

Parameter	Symbol	Value	Unit
Collector-emitter voltage	$V_{\sf CEO}$		V
T _A = 25 °C		4.0	
<i>T</i> _A = − 55 °C		3.5	
Collector-emitter voltage	V_{CES}	13	
Collector-base voltage	V_{CBO}	13	
Emitter-base voltage	V_{EBO}	1.2	
Collector current	IC	30	mA
Base current	I _B	3	
Total power dissipation ¹⁾	P _{tot}	160	mW
<i>T</i> _S ≤ 89 °C			
Junction temperature	T_{J}	150	°C
Ambient temperature	T_{A}	-55 150	
Storage temperature	T _{Stq}	-55 150	

 $^{^{1}}T_{\mathrm{S}}$ is measured on the emitter lead at the soldering point to the pcb

Thermal Resistance

Parameter	Symbol	Value	Unit
Junction - soldering point ¹⁾	R _{thJS}	≤ 380	K/W



Electrical Characteristics at $T_A = 25$ °C, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
DC Characteristics	,		•		•
Collector-emitter breakdown voltage	V _{(BR)CEO}	4	4.7	-	V
$I_{\rm C} = 1 \text{ mA}, I_{\rm B} = 0$					
Collector-emitter cutoff current	I _{CES}	-	1	-	nA
$V_{CE} = 5 \text{ V}, V_{BE} = 0$					
Collector-base cutoff current	I _{CBO}	-	1	-	
$V_{CB} = 5 \text{ V}, I_{E} = 0$					
Emitter-base cutoff current	I _{EBO}	-	10	-	
$V_{\rm EB} = 0.5 \rm V, \it I_{\rm C} = 0$					
DC current gain	h _{FE}	-	250	-	-
$I_{\rm C}$ = 25 V, $V_{\rm CE}$ = 3 V, pulse measured					

 $^{^{1}\}mbox{For calculation of}\,R_{\mbox{\scriptsize thJA}}$ please refer to Application Note Thermal Resistance



Electrical Characteristics at $T_A = 25$ °C, unless otherwise specified

Parameter	Symbol	Values			Unit
	_	min.	typ.	max.	
AC Characteristics (verified by random sampling	g)				
Transition frequency	f_{T}	-	47	-	GHz
$I_{\rm C}$ = 25 mA, $V_{\rm CE}$ = 3 V, f = 2 GHz					
Collector-base capacitance	C _{cb}	-	0.08	-	pF
V_{CB} = 3 V, f=1 MHz, V_{BE} = 0, emitter grounded					
Collector emitter capacitance	C _{ce}	-	0.35	-	
V_{CE} = 3 V, f = 1 MHz, V_{BE} = 0, base grounded					
Emitter-base capacitance	C _{eb}	-	0.45	-	
V_{EB} = 0.5 V, f =1 MHz, V_{CB} =0, collector grounded	k				
Noise figure	F				dB
I_{C} = 8 mA, V_{CE} = 3 V, f = 1.8 GHz, Z_{S} = Z_{Sopt}		-	0.5	_	
I_{C} = 8 mA, V_{CE} = 3 V, f = 6 GHz, Z_{S} = Z_{Sopt}		-	0.85	-	
Power gain	G _{ms}	-	27	_	dB
$I_{\rm C}$ = 25 mA, $V_{\rm CE}$ = 3 V, $Z_{\rm S}$ = $Z_{\rm Sopt}$, $Z_{\rm L}$ = $Z_{\rm Lopt}$,					
f = 1.8 GHz					
Power gain, maximum available ¹⁾	G _{ma}	-	17	-	dB
$I_{\rm C}$ = 25 mA, $V_{\rm CE}$ = 3 V, $Z_{\rm S}$ = $Z_{\rm Sopt,}$ $Z_{\rm L}$ = $Z_{\rm Lopt}$,					
f = 6 GHz					
Transducer gain	$ S_{21e} ^2$				dB
$I_{\rm C}$ = 25 mA, $V_{\rm CE}$ = 3 V, $Z_{\rm S}$ = $Z_{\rm L}$ = 50 Ω ,					
f = 1.8 GHz		-	24.5	-	
f = 6 GHz		-	14	_	
Third order intercept point at output ²⁾	IP ₃	-	25	-	dBm
V_{CE} = 3 V, I_{C} = 25 mA, f = 1.8 GHz,					
$Z_{\rm S} = Z_{\rm L} = 50 \ \Omega$					
1dB Compression point	P _{-1dB}	-	11	-	
$I_{\rm C}$ = 25 mA, $V_{\rm CE}$ = 3 V, $Z_{\rm S}$ = $Z_{\rm L}$ = 50 Ω ,					
f = 1.8 GHz					

 $^{^{1}}G_{\text{ma}} = |S_{21e} / S_{12e}| (k-(k^{2}-1)^{1/2})$

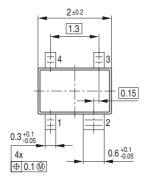
²IP3 value depends on termination of all intermodulation frequency components.

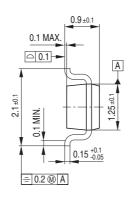
Termination used for this measurement is 50 Ω from 0.1 MHz to 6 GHz



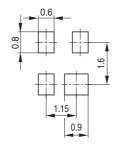
Package Outline



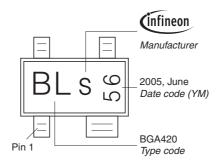




Foot Print

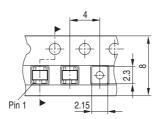


Marking Layout (Example)



Standard Packing

Reel ø180 mm = 3.000 Pieces/Reel Reel ø330 mm = 10.000 Pieces/Reel







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